

# OSRAM SFH 4556

## Datasheet

**Published by ams-OSRAM AG**

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Radial T1 3/4

# SFH 4556

Infrared Emitter (850 nm)



## Applications

- Access control & security
- Home & building automation
- Appliances & tools

## Features

- Package: black epoxy
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)
- High Power Infrared LED
- Short switching times

## Ordering Information

| Type          | Radiant intensity <sup>1)2)</sup><br>$I_F = 100 \text{ mA}; t_p = 20 \text{ ms}$<br>$I_e$ | Radiant intensity <sup>1)</sup><br>typ.<br>$I_F = 100 \text{ mA}; t_p = 20 \text{ ms}$<br>$I_e$ | Ordering Code |
|---------------|-------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------|---------------|
| SFH 4556-VAW  | 71 ... 180 mW/sr                                                                          | 145 mW/sr                                                                                       | Q65110A9803   |
| SFH 4556      | 71 ... 280 mW/sr                                                                          | 145 mW/sr                                                                                       | Q65110A6087   |
| SFH 4556-AW   | 112 ... 180 mW/sr                                                                         | 145 mW/sr                                                                                       | Q65111A9676   |
| SFH 4556-AWBW | 112 ... 280 mW/sr                                                                         | 145 mW/sr                                                                                       | Q65115A2247   |

## Maximum Ratings

 $T_A = 25\text{ °C}$ 

| Parameter                                                                    | Symbol               |              | Values           |
|------------------------------------------------------------------------------|----------------------|--------------|------------------|
| Operating temperature                                                        | $T_{op}$             | min.<br>max. | -40 °C<br>100 °C |
| Storage temperature                                                          | $T_{stg}$            | min.<br>max. | -40 °C<br>100 °C |
| Junction temperature                                                         | $T_j$                | max.         | 100 °C           |
| Forward current                                                              | $I_F$                | min.<br>max. | 1 mA<br>100 mA   |
| Forward current pulsed<br>$t_p \leq 400\text{ }\mu\text{s}$ ; $D \leq 0.005$ | $I_{F\text{ pulse}}$ | max.         | 1 A              |
| Reverse voltage <sup>3)</sup>                                                | $V_R$                | max.         | 5 V              |
| ESD withstand voltage<br>acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)       | $V_{ESD}$            | max.         | 2 kV             |

## Characteristics

$I_F = 100 \text{ mA}$ ;  $t_p = 20 \text{ ms}$ ;  $T_A = 25 \text{ °C}$

| Parameter                                                                               | Symbol                      |              | Values                                 |
|-----------------------------------------------------------------------------------------|-----------------------------|--------------|----------------------------------------|
| Peak wavelength                                                                         | $\lambda_{\text{peak}}$     | typ.         | 860 nm                                 |
| Centroid wavelength                                                                     | $\lambda_{\text{centroid}}$ | typ.         | 850 nm                                 |
| Spectral bandwidth at 50% $I_{\text{rel,max}}$ (FWHM)                                   | $\Delta\lambda$             | typ.         | 30 nm                                  |
| Half angle                                                                              | $\varphi$                   | typ.         | 20 °                                   |
| Dimensions of active chip area                                                          | L x W                       | typ.         | 0.3 x 0.3<br>mm x mm                   |
| Rise time (10% / 90%)<br>$I_F = 100 \text{ mA}$ ; $R_L = 50 \text{ }\Omega$             | $t_r$                       | typ.         | 12 ns                                  |
| Fall time (10% / 90%)<br>$I_F = 100 \text{ mA}$ ; $R_L = 50 \text{ }\Omega$             | $t_f$                       | typ.         | 12 ns                                  |
| Forward voltage <sup>4)</sup>                                                           | $V_F$                       | typ.<br>max. | 1.5 V<br>1.7 V                         |
| Forward voltage <sup>4)</sup><br>$I_F = 1 \text{ A}$ ; $t_p = 100 \text{ }\mu\text{s}$  | $V_F$                       | typ.<br>max. | 2.4 V<br>2.9 V                         |
| Reverse current <sup>3)</sup><br>$V_R = 5 \text{ V}$                                    | $I_R$                       | typ.<br>max. | 0.01 $\mu\text{A}$<br>10 $\mu\text{A}$ |
| Radiant intensity <sup>1)</sup><br>$I_F = 1 \text{ A}$ ; $t_p = 25 \text{ }\mu\text{s}$ | $I_e$                       | typ.         | 1150 mW/sr                             |
| Total radiant flux <sup>5)</sup><br>$I_F = 100 \text{ mA}$ ; $t_p = 20 \text{ ms}$      | $\Phi_e$                    | typ.         | 60 mW                                  |
| Temperature coefficient of voltage                                                      | $TC_V$                      | typ.         | -0.7 mV / K                            |
| Temperature coefficient of brightness                                                   | $TC_I$                      | typ.         | -0.5 % / K                             |
| Temperature coefficient of wavelength                                                   | $TC_\lambda$                | typ.         | 0.3 nm / K                             |
| Thermal resistance junction ambient real <sup>6)</sup>                                  | $R_{\text{thJA}}$           | max.         | 450 K / W                              |

Brightness Groups

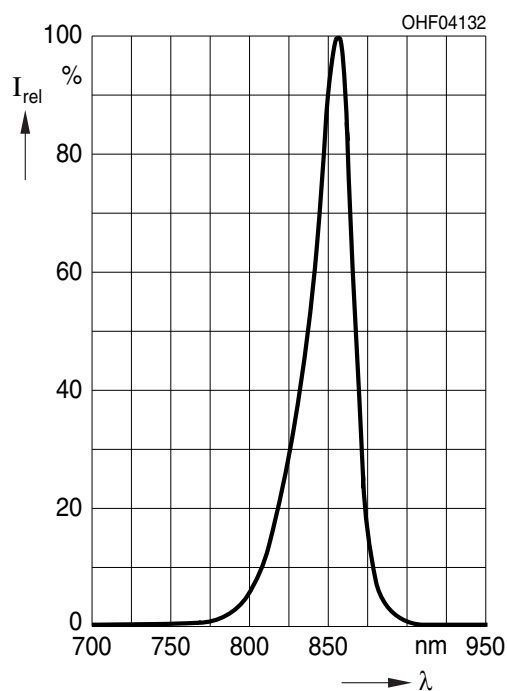
T<sub>A</sub> = 25 °C

| Group | Radiant intensity <sup>1)2)</sup><br>I <sub>F</sub> = 100 mA; t <sub>p</sub> = 20 ms<br>min.<br>I <sub>e</sub> | Radiant intensity <sup>1)2)</sup><br>I <sub>F</sub> = 100 mA; t <sub>p</sub> = 20 ms<br>max.<br>I <sub>e</sub> |
|-------|----------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------|
|       |                                                                                                                |                                                                                                                |
| V     | 71 mW/sr                                                                                                       | 112 mW/sr                                                                                                      |
| AW    | 112 mW/sr                                                                                                      | 180 mW/sr                                                                                                      |
| BW    | 180 mW/sr                                                                                                      | 280 mW/sr                                                                                                      |

Only one group in one packing unit.

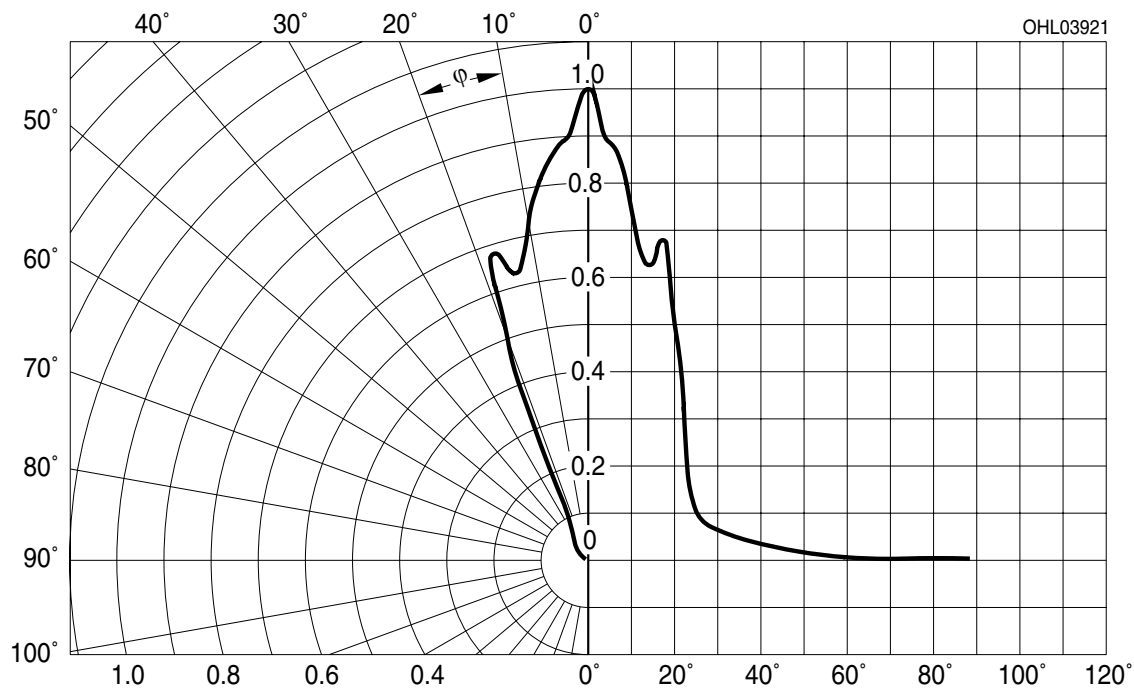
## Relative Spectral Emission 7), 8)

$$I_{e,rel} = f(\lambda); I_F = 100 \text{ mA}; t_p = 20 \text{ ms}$$



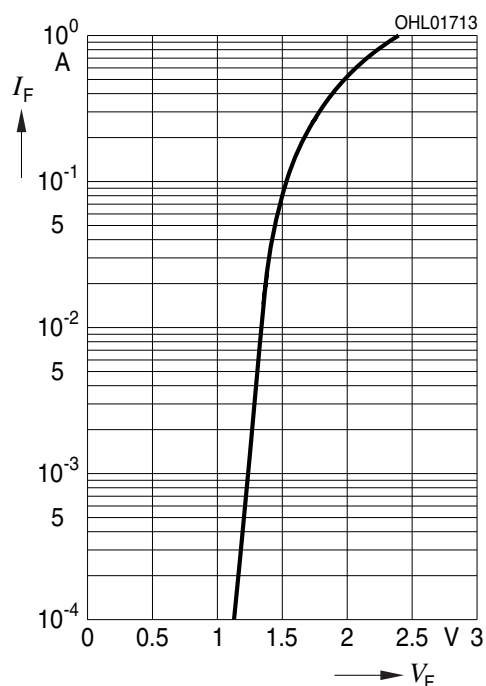
## Radiation Characteristics 7), 8)

$$I_{e,rel} = f(\varphi)$$



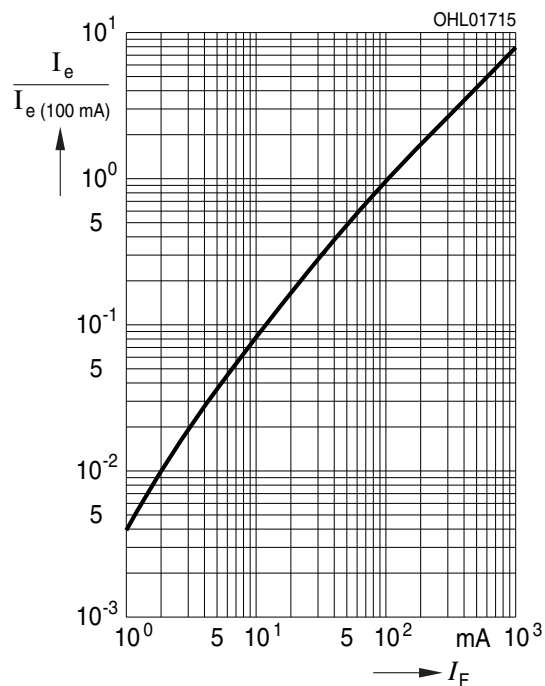
## Forward current 7), 8)

$I_F = f(V_F)$ ; single pulse;  $t_p = 100 \mu s$



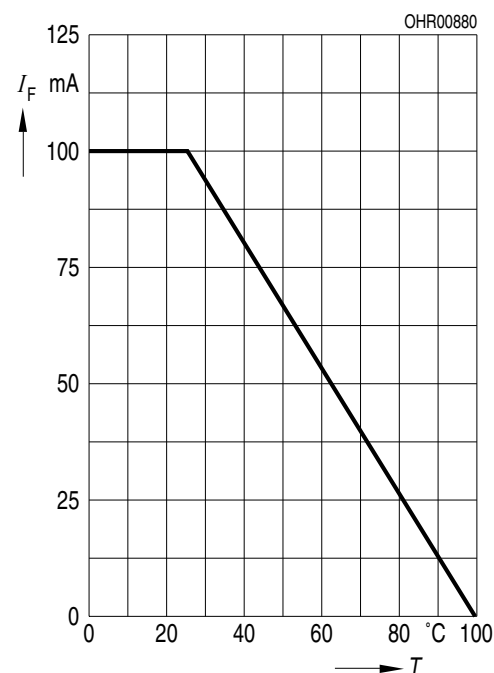
## Radiant Intensity 7), 8)

$I_e/I_e(100mA) = f(I_F)$ ; single pulse;  $t_p = 25 \mu s$



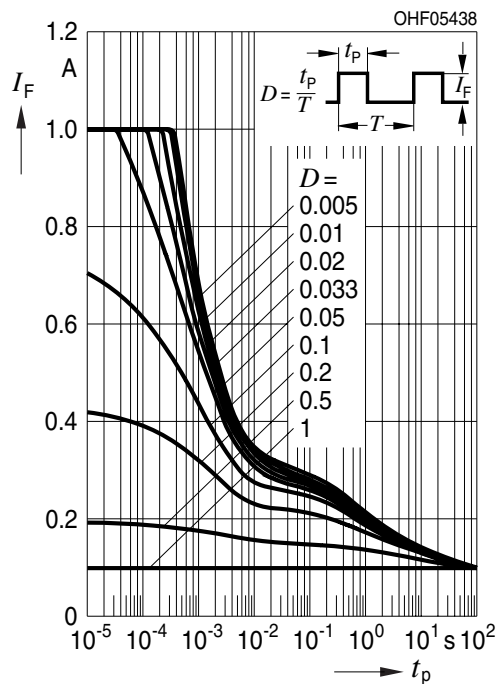
## Max. Permissible Forward Current

$I_F = f(T_A)$ ;  $R_{th_{ja}} = 450 \text{ K/W}$



## Permissible Pulse Handling Capability

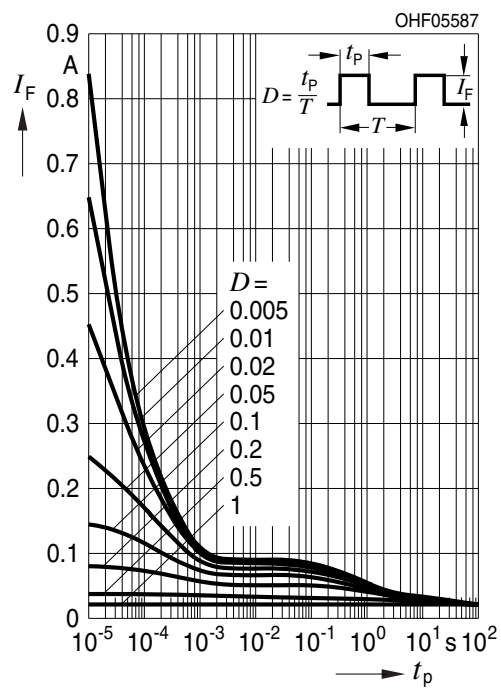
$I_F = f(t_p)$ ; duty cycle  $D = \text{parameter}$ ;  $T_A = 25^\circ\text{C}$



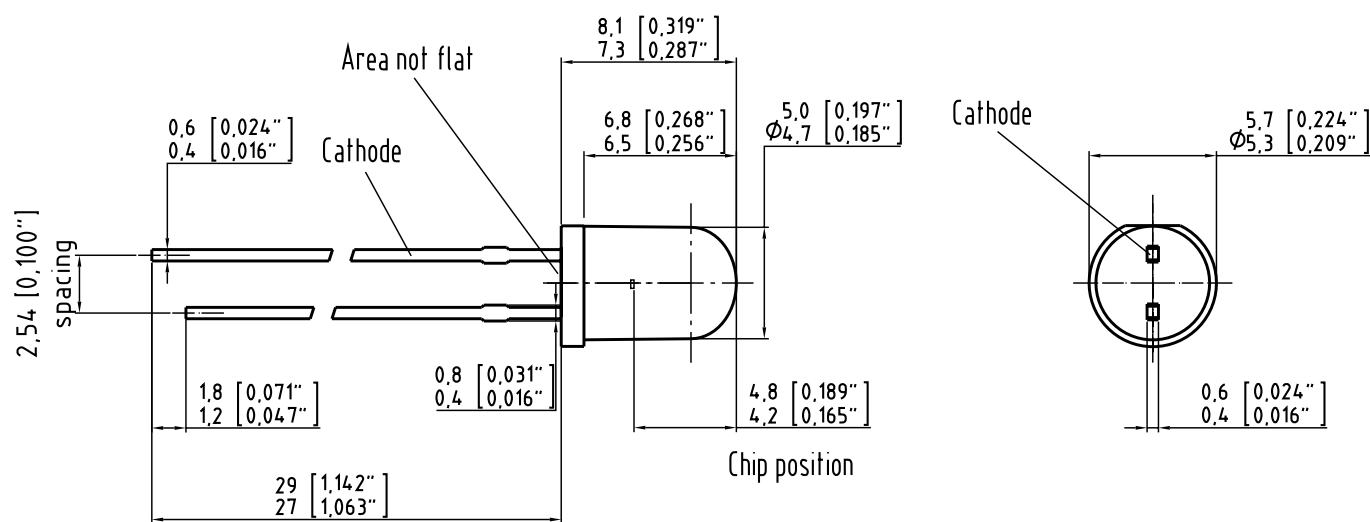


## Permissible Pulse Handling Capability

$I_F = f(t_p)$ ; duty cycle  $D =$  parameter;  $T_A = 85^\circ\text{C}$



## Dimensional Drawing <sup>9)</sup>



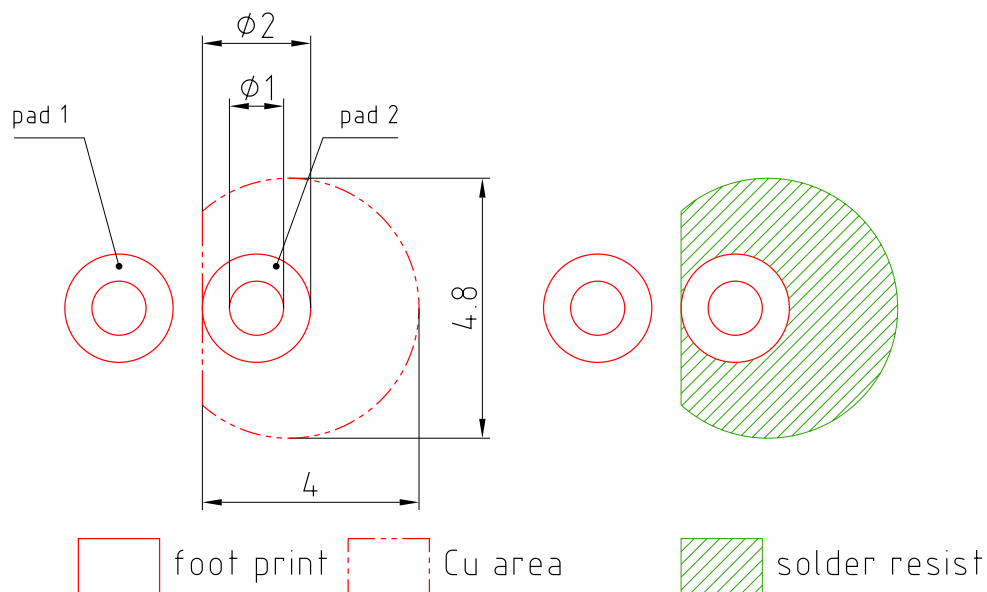
C63062-A3930-A1 -02

### Further Information:

**Approximate Weight:** 298.0 mg

**Package marking:** Cathode

## Recommended Solder Pad <sup>9)</sup>

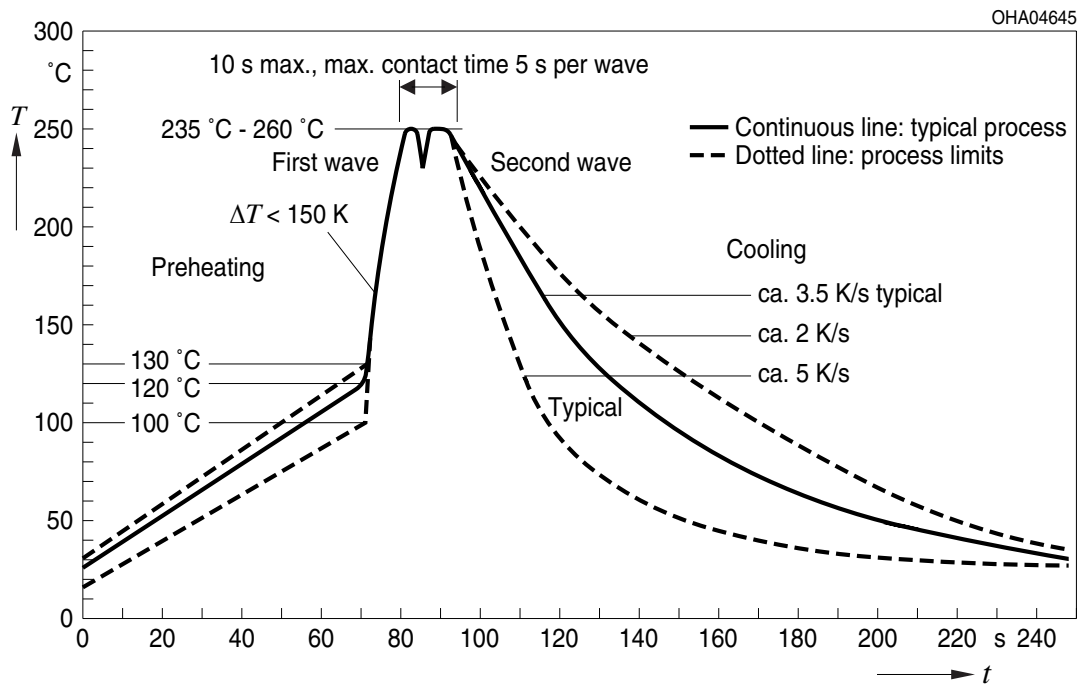


E062.3010.188-01

Pad 1: cathode

## TTW Soldering

IEC-61760-1 TTW



## Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet falls into **exempt risk group - Exempt**.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

Packing information is available on the internet (online product catalog).

For further application related information please visit <https://ams-osram.com/support/application-notes>

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## Disclaimer

### Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

### Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

### Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.

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## Glossary

- 1) **Radiant intensity:** Measured at a solid angle of  $\Omega = 0.01$  sr
- 2) **Brightness:** The brightness values are measured with a tolerance of  $\pm 11\%$ .
- 3) **Reverse Operation:** This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- 4) **Forward Voltage:** The forward voltages are measured with a tolerance of  $\pm 0.1$  V.
- 5) **Total radiant flux:** Measured with integrating sphere.
- 6) **Thermal resistance:** junction - ambient, mounted on PC-board (FR4), padsize 16 mm<sup>2</sup> each
- 7) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 8) **Testing temperature:** TA = 25°C (unless otherwise specified)
- 9) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with  $\pm 0.1$  and dimensions are specified in mm.

Revision History

| Version | Date       | Change                             |
|---------|------------|------------------------------------|
| 1.5     | 2021-09-21 | Maximum Ratings                    |
| 1.6     | 2021-10-13 | Maximum Ratings<br>Characteristics |
| 1.7     | 2021-11-18 | Features                           |
| 1.8     | 2022-08-09 | Applications<br>New Layout         |
| 1.9     | 2026-07-02 | Ordering Information               |



EU RoHS and China RoHS compliant product

此产品符合欧盟 RoHS 指令的要求；  
按照中国的相关法规和标准，  
不含有毒有害物质或元素。

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